

LAMINATE, RESIN COMPOSITION, AND METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE

ABSTRACT

Provided is a laminate that allows semiconductor elements to be transferred over a wide range of processing margins using lasers of various wavelengths, without damaging the elements or leaving behind any pasty residue. This laminate is a substrate in which a laser-transmitting substrate 1, a resin film, and a semiconductor element are laminated in the stated order. The absorbance of the resin film at a wavelength of 248 nm, 266 nm, or 355 nm expressed in terms of a film thickness of 1.0 μm is 0.4-5.0, and the adhesive strength of the resin film with respect to the semiconductor elements is 0.02-0.3 N/cm.

[FIG. 2]